

**ADVANCED INFORMATION**

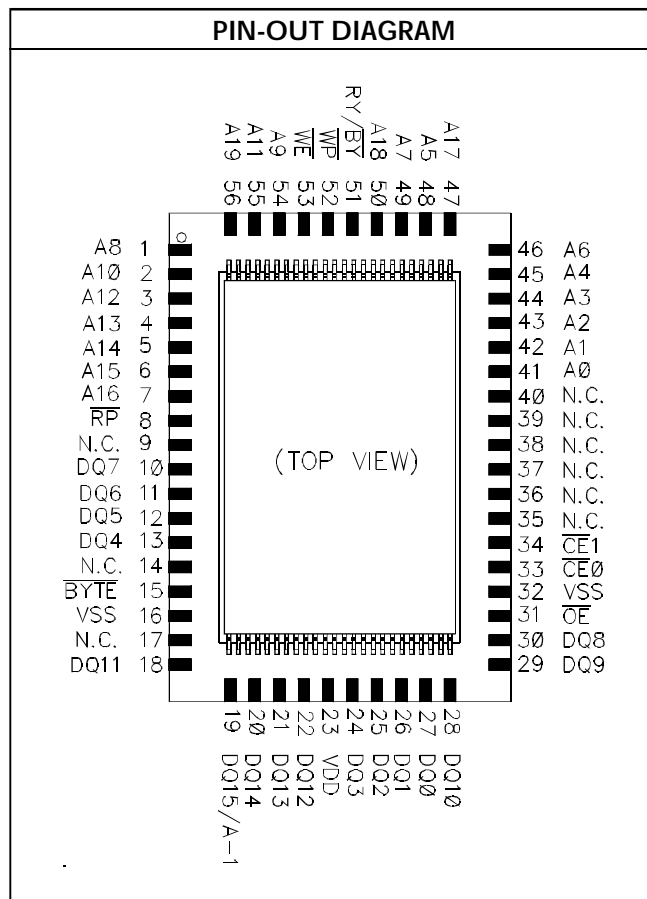
**DESCRIPTION:**

The DP3Z2MX16PMTY5/DP3Z2MX16PMBY5 is a 32 megabit 3.3 Volt only CMOS Flash EEPROM (Electrically In-System Programmable and Erasable ROM Memory) module. These modules are constructed of two 1M x 16 FLASH EEPROM's that are configured as a 2M x 16.

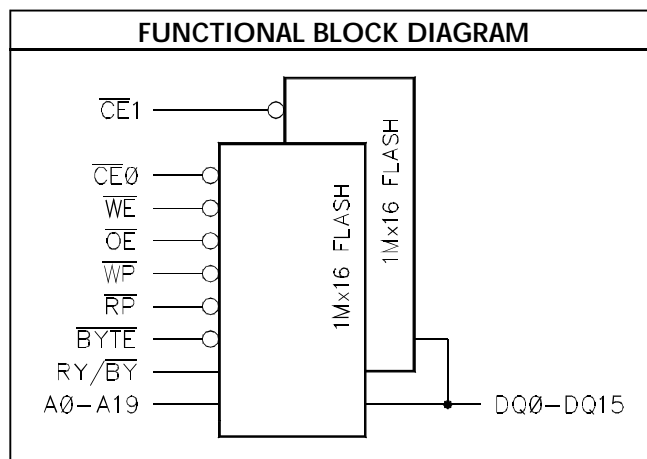
The module features high speed access times with common data inputs and outputs. The Flash devices used in this module also features BGO (Blank Ground Operations). This feature allows Program or Erase operations to be performed on one bank of the device while a read operation is performed on the other bank.

**FEATURES:**

- Organizations Available: 2M x 16
- Fast Read Access Times: 80ns ( $V_{DD} = 3.3 \pm 0.3V$ )  
90ns ( $V_{DD} = 2.7 \sim 3.6V$ )
- Industrial Temperature:  $-40^{\circ}C$  to  $+85^{\circ}C$
- Low Power:
  - 70 mA Maximum active (16 bit Mode)
  - 10 $\mu$ A Maximum Standby (CMOS)
- 100K Program / Erase Cycles
- 3.3 Volt Only In-System Programming
- Package: 56-Pin TSOP Stack

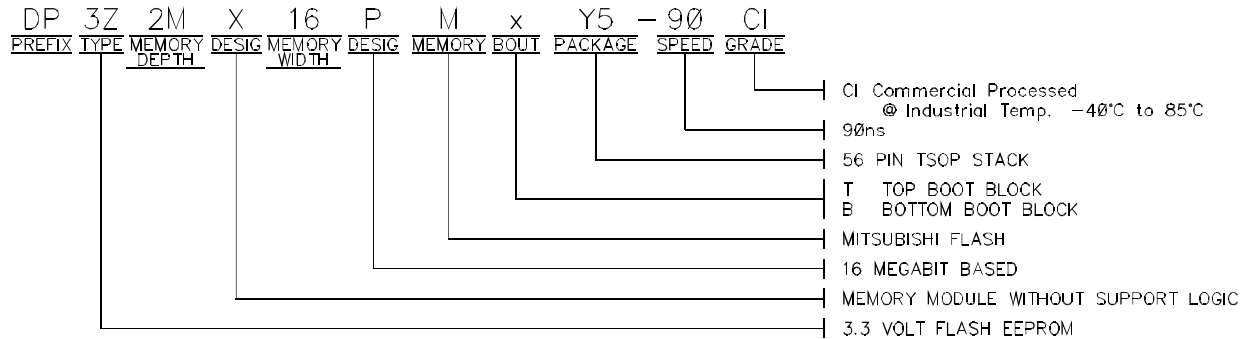


PIN NAMES	
A0 - A19	Address
DQ0 - DQ15	Data Input / Output
CE0, CE1	Low Chip Enables
WE	Write Enable
OE	Output Enable
WP	Write Protect
RP	Reset/Power Down
BYTE	Byte Enable
RY/BY	Ready/Busy
V <sub>DD</sub>	Power (+3.3V)
VSS	Ground
N.C.	No Connect

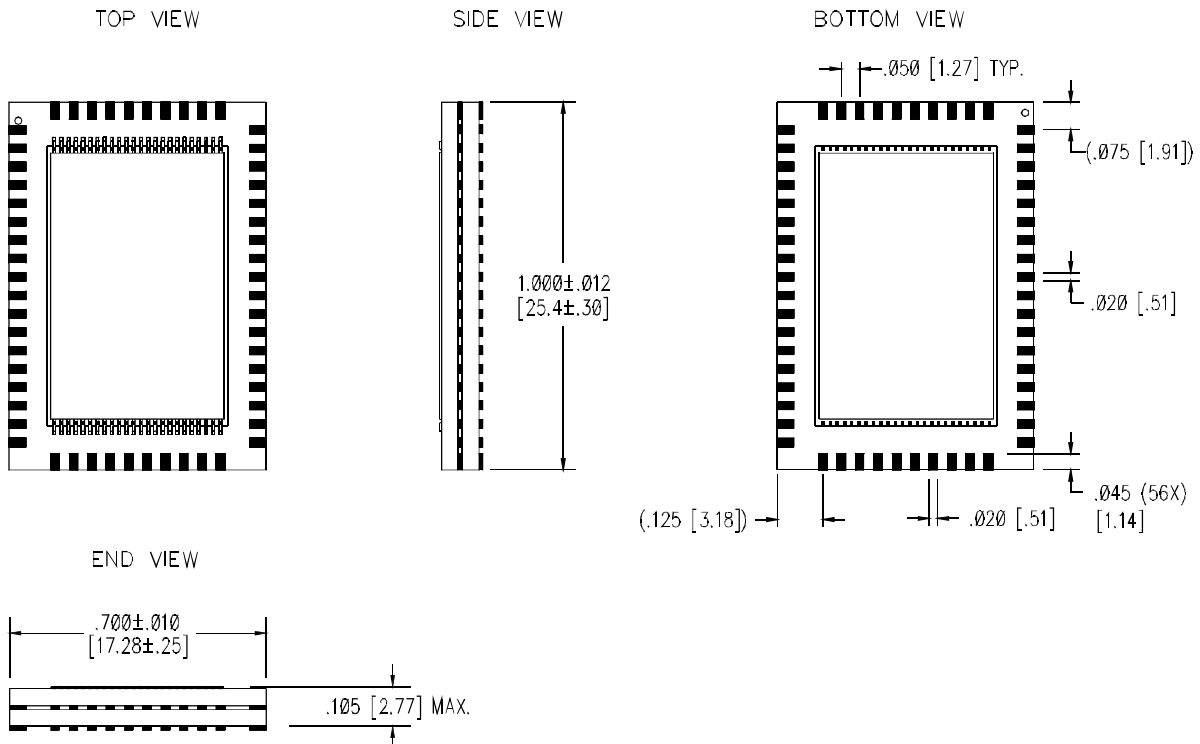


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**Dense-Pac Microsystems, Inc.**

7321 Lincoln Way, Garden Grove, California 92841-1431

(714) 898-0007 ◆ (800) 642-4477 ◆ FAX: (714) 897-1772 ◆ <http://www.dense-pac.com>